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Publications

Book Chapter

Kumar S., Sharma T. K. (2021) On-Chip Carbon Nanotube Interconnects: Adaptation to Multi-gate Transistors. In: Kaneko S. et al. (eds) Carbon Related Materials. Springer, Singapore. https://doi.org/10.1007/978-981-15-7610-2_7 [Recognition of Nobel Lecture by Prof. Akira Suzuki in IUMRS-ICAM-17]

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